# WEST Search History

| Hide Items | Restore | Clear | Cancel |

DATE: Friday, March 19, 2004

| Hide? | Set Name | Query | Hit Count |
|---|---|---|---|
| | | *DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR* | |
| ☐ | L36 | l34 and l11 | 57 |
| ☐ | L35 | l34 and l11 | 57 |
| ☐ | L34 | channel adj7 oxide | 15617 |
| ☐ | L33 | cahnnel adj4 oxide | 0 |
| ☐ | L32 | cahnnel adj4 oxide | 0 |
| ☐ | L31 | 5216262 | 22 |
| | | *DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR* | |
| ☐ | L30 | 5216262 | 22 |
| ☐ | L29 | 6472685 | 3 |
| | | *DB=EPAB; PLUR=YES; OP=OR* | |
| ☐ | L28 | 2347520 | 1 |
| | | *DB=DWPI; PLUR=YES; OP=OR* | |
| ☐ | L27 | L26 and l25 | 2 |
| ☐ | L26 | tsu.inv. | 80 |
| ☐ | L25 | L24 and l23 | 63 |
| ☐ | L24 | barrier and silicon | 5445 |
| ☐ | L23 | wang.inv. | 40396 |
| ☐ | L22 | 02103767 | 0 |
| ☐ | L21 | 02/103767 | 0 |
| | | *DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR* | |
| ☐ | L20 | l1 and l19 | 8 |
| ☐ | L19 | l11 adj20 l18 | 655 |
| ☐ | L18 | oxide or nitride o fluorine or carbon or carbide | 6180325 |
| ☐ | L17 | 6699771 | 1 |
| ☐ | L16 | l2 and l14 and l15 | 16 |
| ☐ | L15 | oxygen or o?sub.$ | 811012 |
| ☐ | L14 | silicon or si | 1786914 |
| ☐ | L13 | l7 and l5 | 56 |
| ☐ | L12 | l11 and l18 | 0 |
| ☐ | L11 | superlattice | 7764 |
| ☐ | L10 | l2 and l8 | 0 |

| | | | |
|---|---|---|---:|
| ☐ | L9 | band-modif$5 | 0 |
| ☐ | L8 | band adj modif$5 | 262 |
| ☐ | L7 | band adj modif$5 or band-modi$4 | 262 |
| ☐ | L6 | l2 and l5 | 36 |
| ☐ | L5 | monolayer mono$5 or atom$5 | 1483361 |
| ☐ | L4 | L3 and l2 | 27 |
| ☐ | L3 | parallel | 2304355 |
| ☐ | L2 | superlattice adj6 channel | 104 |
| ☐ | L1 | superlattice adj6 channel | 104 |

END OF SEARCH HISTORY

# Refine Search

## Search Results -

| Terms | Documents |
|---|---|
| L18 and L17 | 2 |

**Database:**

```
US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins
```

**Search:**

L19

Refine Search

Recall Text    Clear              Interrupt

---

## Search History

**DATE: Friday, March 19, 2004**    Printable Copy    Create Case

| Set Name side by side | Query | Hit Count | Set Name result set |
|---|---|---|---|
| *DB=DWPI; PLUR=YES; OP=OR* | | | |
| L19 | L18 and 117 | 2 | L19 |
| L18 | lofgren.inv. | 172 | L18 |
| L17 | L16 and 115 | 20 | L17 |
| L16 | wang.inv. | 40396 | L16 |
| L15 | tsu.inv. | 80 | L15 |
| L14 | 2103767 | 7 | L14 |
| L13 | 02103767 | 0 | L13 |
| *DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR* | | | |
| L12 | l1 near20 l2 | 5 | L12 |
| L11 | L10 near10 l1 | 34 | L11 |
| L10 | tilt | 166799 | L10 |
| L9 | l1 and l8 | 4 | L9 |
| L8 | 5679152 | 55 | L8 |
| L7 | l3 and l6 | 154 | L7 |

# WEST Search History

DATE: Friday, March 19, 2004

| Hide? | Set Name | Query | Hit Count |
|---|---|---|---|
| | | DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR | |
| ☐ | L20 | l1 and l19 | 8 |
| ☐ | L19 | l11 adj20 l18 | 655 |
| ☐ | L18 | oxide or nitride o fluorine or carbon or carbide | 6180325 |
| ☐ | L17 | 6699771 | 1 |
| ☐ | L16 | l2 and l14 and l15 | 16 |
| ☐ | L15 | oxygen or o?sub.$ | 811012 |
| ☐ | L14 | silicon or si | 1786914 |
| ☐ | L13 | l7 and l5 | 56 |
| ☐ | L12 | l11 and l18 | 0 |
| ☐ | L11 | superlattice | 7764 |
| ☐ | L10 | l2 and l8 | 0 |
| ☐ | L9 | band-modif$5 | 0 |
| ☐ | L8 | band adj modif$5 | 262 |
| ☐ | L7 | band adj modif$5 or band-modi$4 | 262 |
| ☐ | L6 | l2 and l5 | 36 |
| ☐ | L5 | monolayer mono$5 or atom$5 | 1483361 |
| ☐ | L4 | L3 and l2 | 27 |
| ☐ | L3 | parallel | 2304355 |
| ☐ | L2 | superlattice adj6 channel | 104 |
| ☐ | L1 | superlattice adj6 channel | 104 |

END OF SEARCH HISTORY

# Hit List

Search Results - Record(s) 1 through 16 of 16 returned.

---

☐ 1. Document ID: US 6559469 B1

**Using default format because multiple data bases are involved.**

L16: Entry 1 of 16                         File: USPT                May 6, 2003

US-PAT-NO: 6559469
DOCUMENT-IDENTIFIER: US 6559469 B1

TITLE: Ferroelectric and high dielectric constant transistors

DATE-ISSUED: May 6, 2003

INVENTOR-INFORMATION:

| NAME | CITY | STATE | ZIP CODE | COUNTRY |
|------|------|-------|----------|---------|
| Paz de Araujo; Carlos A. | Colorado Springs | CO | | |
| McMillan; Larry D. | Colorado Springs | CO | | |
| Joshi; Vikram | Colorado Springs | CO | | |
| Solayappan; Narayan | Colorado Springs | CO | | |
| Cuchiaro; Joseph D. | Colorado Springs | CO | | |

US-CL-CURRENT: 257/15; 257/16, 257/17, 257/18, 257/19, 257/20, 257/21, 257/22, 257/295, 257/E21.011, 257/E21.272, 257/E27.085, 257/E27.104

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D

---

☐ 2. Document ID: US 6426536 B1

L16: Entry 2 of 16                         File: USPT                Jul 30, 2002

US-PAT-NO: 6426536
DOCUMENT-IDENTIFIER: US 6426536 B1

TITLE: Double layer perovskite oxide electrodes

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D

---

☐ 3. Document ID: US 6355951 B1

L16: Entry 3 of 16                         File: USPT                Mar 12, 2002

US-PAT-NO: 6355951
DOCUMENT-IDENTIFIER: US 6355951 B1

TITLE: Field effect semiconductor device

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D- |

---

☐ 4. Document ID: US 6294446 B1
L16: Entry 4 of 16                    File: USPT                    Sep 25, 2001

US-PAT-NO: 6294446
DOCUMENT-IDENTIFIER: US 6294446 B1

TITLE: Methods of manufacturing a high electron mobility transistor with a T-shaped gate electrode

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D- |

---

☐ 5. Document ID: US 5952672 A
L16: Entry 5 of 16                    File: USPT                    Sep 14, 1999

US-PAT-NO: 5952672
DOCUMENT-IDENTIFIER: US 5952672 A

TITLE: Semiconductor device and method for fabricating the same

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D- |

---

☐ 6. Document ID: US 5760418 A
L16: Entry 6 of 16                    File: USPT                    Jun 2, 1998

US-PAT-NO: 5760418
DOCUMENT-IDENTIFIER: US 5760418 A

TITLE: GaAs power semiconductor device operating at a low voltage and method for fabricating the same

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D- |

---

☐ 7. Document ID: US 5639677 A
L16: Entry 7 of 16                    File: USPT                    Jun 17, 1997

US-PAT-NO: 5639677
DOCUMENT-IDENTIFIER: US 5639677 A

TITLE: Method of making a gaAs power semiconductor device operating at a low

voltage

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

☐  8.   Document ID: US 5432356 A

L16: Entry 8 of 16                    File: USPT                    Jul 11, 1995

US-PAT-NO: 5432356
DOCUMENT-IDENTIFIER: US 5432356 A

TITLE: Semiconductor heterojunction floating layer memory device and method for storing information in the same

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

☐  9.   Document ID: US 5430310 A

L16: Entry 9 of 16                    File: USPT                    Jul 4, 1995

US-PAT-NO: 5430310
DOCUMENT-IDENTIFIER: US 5430310 A

TITLE: Field effect transistor

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

☐  10.   Document ID: US 5155053 A

L16: Entry 10 of 16                    File: USPT                    Oct 13, 1992

US-PAT-NO: 5155053
DOCUMENT-IDENTIFIER: US 5155053 A

TITLE: Method of forming T-gate structure on microelectronic device substrate

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

☐  11.   Document ID: US 5055887 A

L16: Entry 11 of 16                    File: USPT                    Oct 8, 1991

US-PAT-NO: 5055887
DOCUMENT-IDENTIFIER: US 5055887 A

TITLE: FET with a super lattice channel

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

☐  12.   Document ID: US 5021839 A

L16: Entry 12 of 16                    File: USPT                    Jun 4, 1991

US-PAT-NO: 5021839
DOCUMENT-IDENTIFIER: US 5021839 A

TITLE: FET with a super lattice channel

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

---

☐  13.   Document ID: US 5008211 A

L16: Entry 13 of 16                    File: USPT                    Apr 16, 1991

US-PAT-NO: 5008211
DOCUMENT-IDENTIFIER: US 5008211 A

TITLE: Method for forming FET with a super lattice channel

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

---

☐  14.   Document ID: US 4945393 A

L16: Entry 14 of 16                    File: USPT                    Jul 31, 1990

US-PAT-NO: 4945393
DOCUMENT-IDENTIFIER: US 4945393 A

TITLE: Floating gate memory circuit and apparatus

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

---

☐  15.   Document ID: US 4905063 A

L16: Entry 15 of 16                    File: USPT                    Feb 27, 1990

US-PAT-NO: 4905063
DOCUMENT-IDENTIFIER: US 4905063 A

TITLE: Floating gate memories

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw D |

---

☐  16.   Document ID: US 4799087 A

L16: Entry 16 of 16                    File: USPT                    Jan 17, 1989

US-PAT-NO: 4799087